

MOSFETs Silicon N-channel MOS (U-MOSVIII-H)

TPH4R606NH

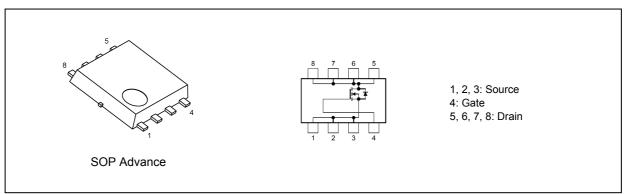
1. Applications

- · Switching Voltage Regulators
- · Motor Drivers
- · DC-DC Converters

2. Features

- (1) Small footprint due to a small and thin package
- (2) High-speed switching
- (3) Small gate charge: $Q_{SW} = 19 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 3.8 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (5) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 60 \text{ V)}$
- (6) Enhancement mode: $V_{th} = 2.0 \text{ to } 4.0 \text{ V } (V_{DS} = 10 \text{ V}, I_D = 0.5 \text{ mA})$

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

| Characterist | ics | | Symbol | Rating | Unit |
|-------------------------------|-------------------------|--------------------|------------------|------------|------|
| Drain-source voltage | | | V_{DSS} | 60 | V |
| Gate-source voltage | | | V_{GSS} | ±20 | |
| Drain current (DC) | (Silicon limit) | (Note 1), (Note 2) | I _D | 85 | Α |
| Drain current (DC) | | (Note 1) | I _D | 32 | |
| Drain current (pulsed) | (t = 1 ms) | (Note 1) | I _{DP} | 96 | |
| Power dissipation | (T _c = 25°C) | | P _D | 63 | W |
| Power dissipation | (t = 10 s) | (Note 3) | P_{D} | 2.8 | W |
| Power dissipation | (t = 10 s) | (Note 4) | P_{D} | 1.6 | W |
| Single-pulse avalanche energy | | (Note 5) | E _{AS} | 133 | mJ |
| Avalanche current | | | I _{AR} | 32 | Α |
| Channel temperature | | | T _{ch} | 150 | °C |
| Storage temperature | | | T _{stg} | -55 to 150 | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

2011-11



5. Thermal Characteristics

| Characteristics | | | | Max | Unit |
|---------------------------------------|-----------------------|----------|-----------------------|------|------|
| Channel-to-case thermal resistance | $(T_c = 25^{\circ}C)$ | | R _{th(ch-c)} | 1.98 | °C/W |
| Channel-to-ambient thermal resistance | (t = 10 s) | (Note 3) | R _{th(ch-a)} | 44.6 | °C/W |
| Channel-to-ambient thermal resistance | (t = 10 s) | (Note 4) | R _{th(ch-a)} | 78.1 | °C/W |

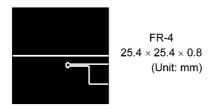
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Limited by silicon capability. Package limit is 60 A.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_{DD} = 24 V, T_{ch} = 25°C (initial), L = 0.18 mH, R_G = 1 Ω , I_{AR} = 32 A



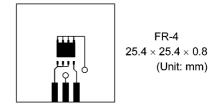


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

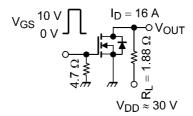
6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|----------------------|---|-----|------|------|------|
| Gate leakage current | I _{GSS} | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±0.1 | μΑ |
| Drain cut-off current | I _{DSS} | V _{DS} = 60 V, V _{GS} = 0 V | _ | _ | 10 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 60 | | _ | V |
| Drain-source breakdown voltage (Note 6) | V _{(BR)DSX} | $I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$ | 45 | | _ | |
| Gate threshold voltage | V_{th} | V _{DS} = 10 V, I _D = 0.5 mA | 2.0 | _ | 4.0 | |
| Drain-source on-resistance | R _{DS(ON)} | V _{GS} = 6.5 V, I _D = 16 A | _ | 5.0 | 11 | mΩ |
| | | V _{GS} = 10 V, I _D = 16 A | | 3.8 | 4.6 | |

Note 6: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|------|------|
| Input capacitance | C _{iss} | V _{DS} = 30 V, V _{GS} = 0 V, f = 1 MHz | _ | 3050 | 3965 | pF |
| Reverse transfer capacitance | C _{rss} | | | 60 | 115 | |
| Output capacitance | C _{oss} | | | 990 | | |
| Gate resistance | r _g | V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz | _ | 1.0 | 1.5 | Ω |
| Switching time (rise time) | t _r | See Figure 6.2.1. | | 10 | _ | ns |
| Switching time (turn-on time) | t _{on} | | _ | 24 | _ | |
| Switching time (fall time) | t _f | | _ | 14 | _ | |
| Switching time (turn-off time) | t _{off} | | _ | 37 | _ | |



Duty \leq 1%, $t_{\text{W}}=$ 10 μs

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Q_g | $V_{DD} \approx 48 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 32 \text{ A}$ | 1 | 49 | 1 | nC |
| Gate-source charge 1 | Q _{gs1} | | | 13 | | |
| Gate-drain charge | Q_{gd} | | _ | 15 | | |
| Gate switch charge | Q_{SW} | | | 19 | | |

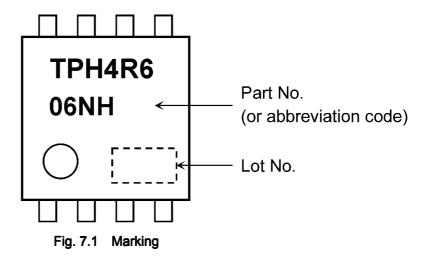
6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------|------------------|---|-----|------|------|------|
| Reverse drain current (pulsed) | (Note 7) | I _{DRP} | _ | _ | _ | 96 | Α |
| Diode forward voltage | | V_{DSF} | I _{DR} = 32 A, V _{GS} = 0 V | _ | _ | -1.2 | V |

Note 7: Ensure that the channel temperature does not exceed 150°C.



7. Marking



8. Characteristics Curves (Note)

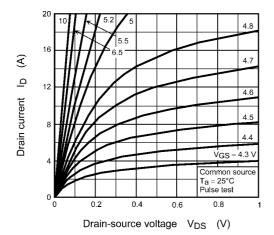


Fig. 8.1 I_D - V_{DS}

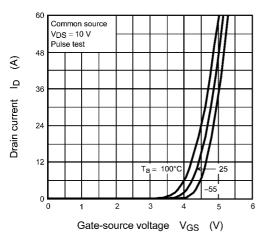


Fig. 8.3 I_D - V_{GS}

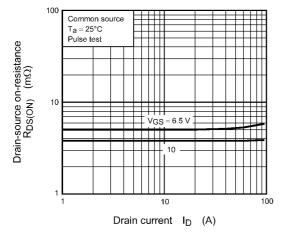


Fig. 8.5 R_{DS(ON)} - I_D

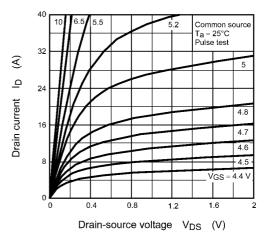


Fig. 8.2 I_D - V_{DS}

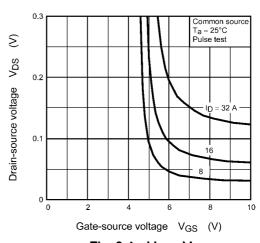


Fig. 8.4 V_{DS} - V_{GS}

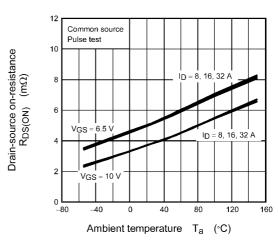


Fig. 8.6 R_{DS(ON)} - T_a

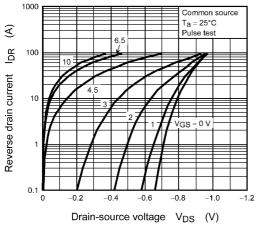


Fig. 8.7 I_{DR} - V_{DS}

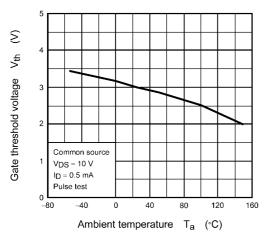


Fig. 8.9 V_{th} - T_a

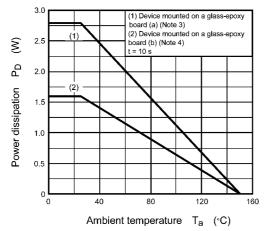


Fig. 8.11 P_D - T_a (Guaranteed Maximum)

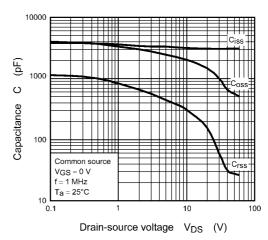


Fig. 8.8 Capacitance - V_{DS}

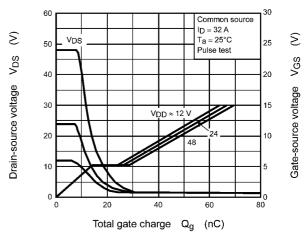


Fig. 8.10 Dynamic Input/Output Characteristics

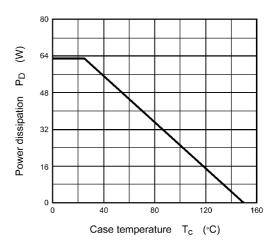


Fig. 8.12 P_D - T_c (Guaranteed Maximum)

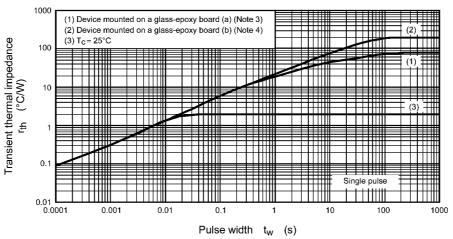


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

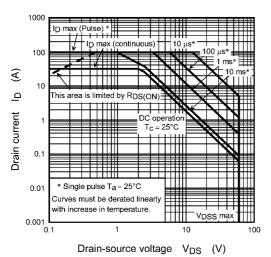


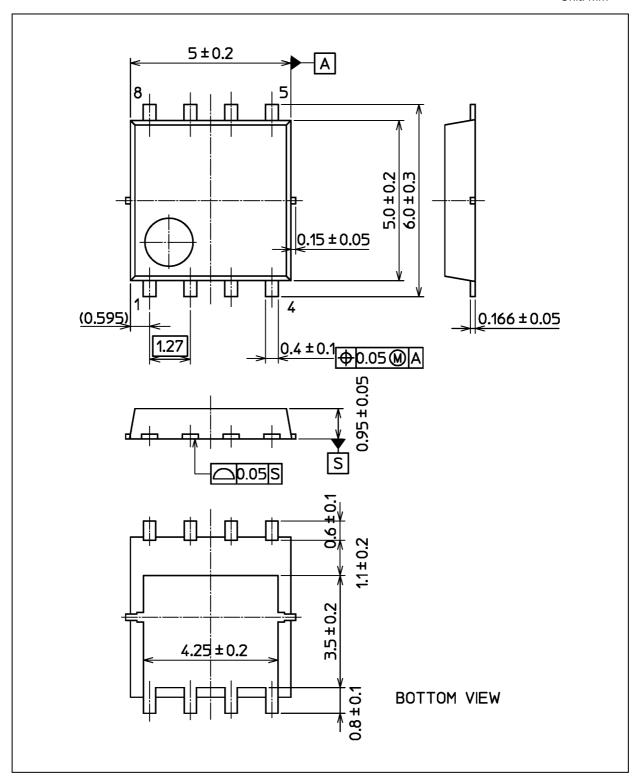
Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.069 g (typ.)

| Package Na | me(s) |
|-----------------------|-------|
| TOSHIBA: 2-5Q1S | |
| Nickname: SOP Advance | |



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